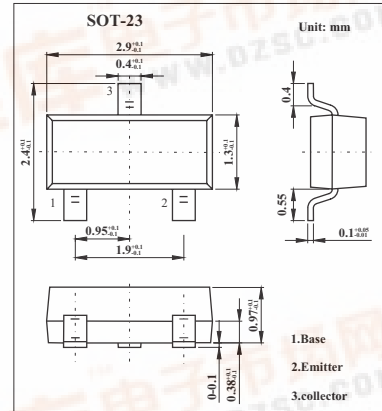


SMD Type Transistors

High Voltage Transistor
BSS63R

■ Features

- SOT23 PNP silicon planar



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-110	V
Collector-emitter voltage	V _{CE0}	-100	V
Emitter-base voltage	V _{EB0}	-6	V
Continuous collector current	I _c	-100	mA
Power dissipation	P _{tot}	330	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA	-110			V
Collector-emitter breakdown voltage *	V _{(BR)CEO}	I _C =-100μA	-100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA	-6			V
Collector-base cut-off current	I _{CBO}	V _{CB} =-90V V _{CB} =-90V, T _a = 150°C			-100 -50	nA μA
Emitter-base current	I _{EBO}	V _{EB} =-6V			-200	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-25mA, I _B =-2.5mA			-250	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-25mA, I _B =-2.5mA			-900	V
DC current gain	h _{FE}	I _C =-10mA, V _{CE} =-1V I _C =-25mA, V _{CE} =-1V	30 30			
Transitional frequency	f _T	I _C =25mA, V _{CE} =-5V, f=35MHz	50	85		MHz
Output capacitance	C _{obo}	V _{CB} =-10V, f=1MHz		3		pF

* Pulse test: t_p = 300 μs; d ≤ 0.02.

■ Marking

Marking	T6
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